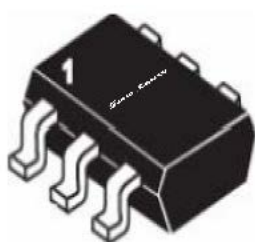
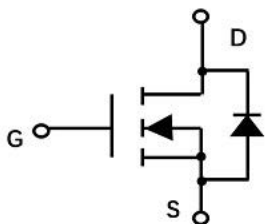
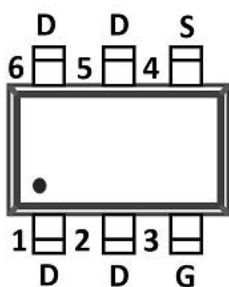


N-Channel Enhancement Mode Field Effect Transistor



SOT-23-6L



Product Summary

- V_{DS} 30V
- I_D 9A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<15m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) $<18m\Omega$

General Description

- Trench Power LV MOSFET technology
- High density cell design for low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	9	A
	$T_A=70^\circ\text{C}$		7.2	
Pulsed Drain Current ^A		I_{DM}	50	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$		P_D	1.25	W
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction and Storage Temperature Range		T_J, T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
SCJ09N03A	F2	0309	3000	30000	120000	7"

■ Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}= \pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=6.0A$		9	15	m Ω
		$V_{GS}=4.5V, I_D=5.0A$		12	18	
Diode Forward Voltage	V_{SD}	$I_S=9A, V_{GS}=0V$			1.2	V
Maximum Body-Diode Continuous Current	I_S				9	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		1015		pF
Output Capacitance	C_{oss}			201		
Reverse Transfer Capacitance	C_{rss}			164		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		23.6		nC
Gate-Source Charge	Q_{gs}			3.9		
Gate-Drain Charge	Q_{gd}			7.0		
Reverse Recovery Chrage	Q_{rr}	$I_F=15A, di/dt=100A/us$		0.1		
Reverse Recovery Time	t_{rr}			7		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=20V, I_D=2A, R_{GEN}=3\Omega$		7		ns
Turn-on Rise Time	t_r			19		
Turn-off Delay Time	$t_{D(off)}$			24		
Turn-off fall Time	t_f			24		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JL}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

■ Typical Performance Characteristics

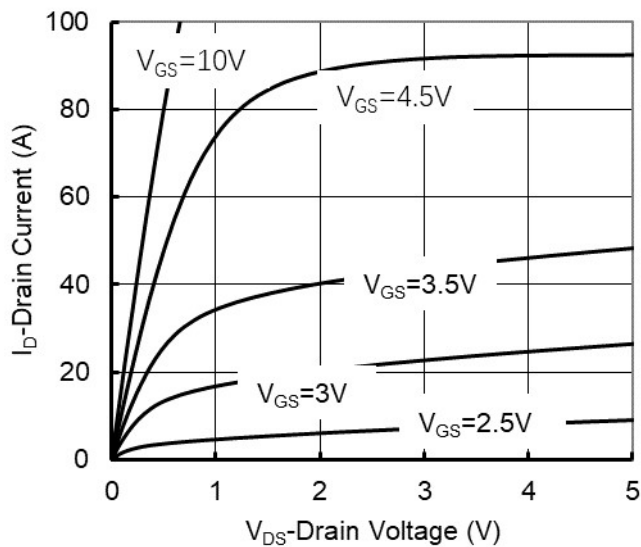


Figure1. Output Characteristics

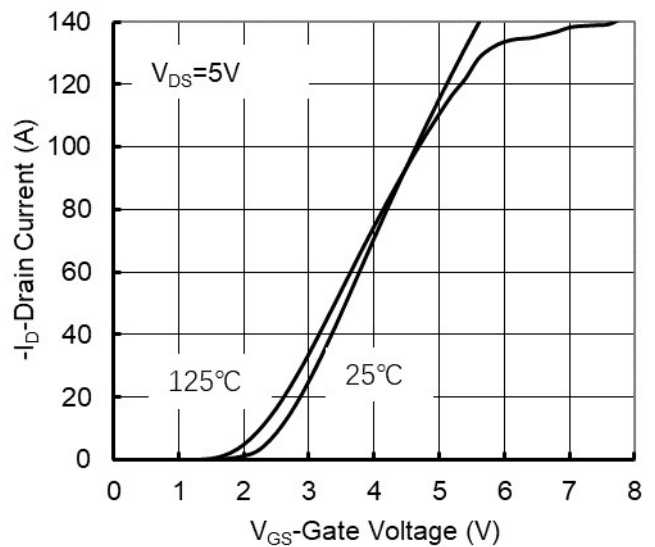


Figure2. Transfer Characteristics

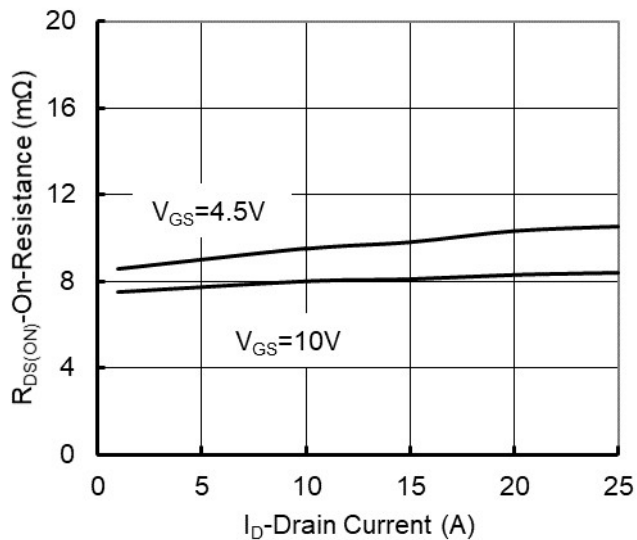


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

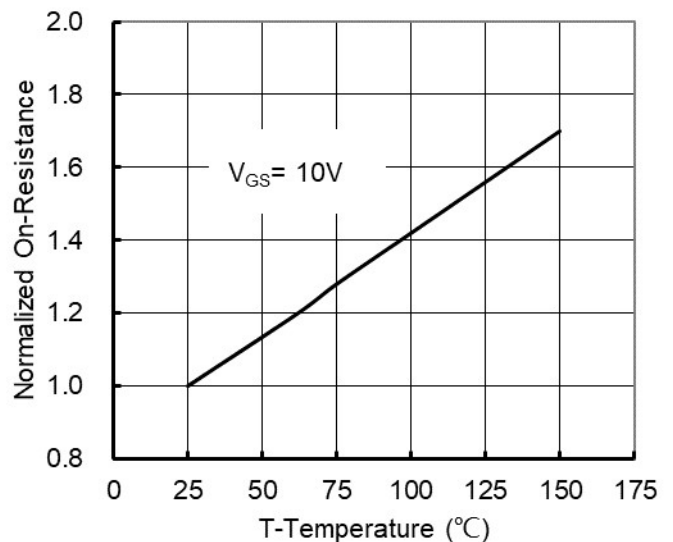


Figure 4: On-Resistance vs. Junction Temperature

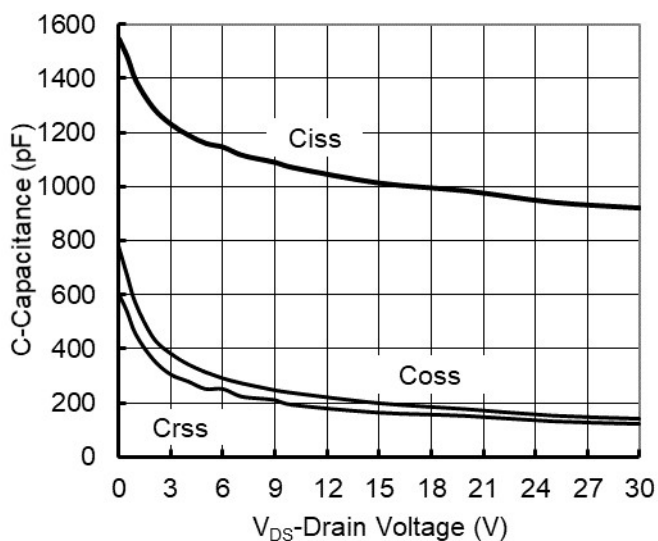


Figure5. Capacitance Characteristics

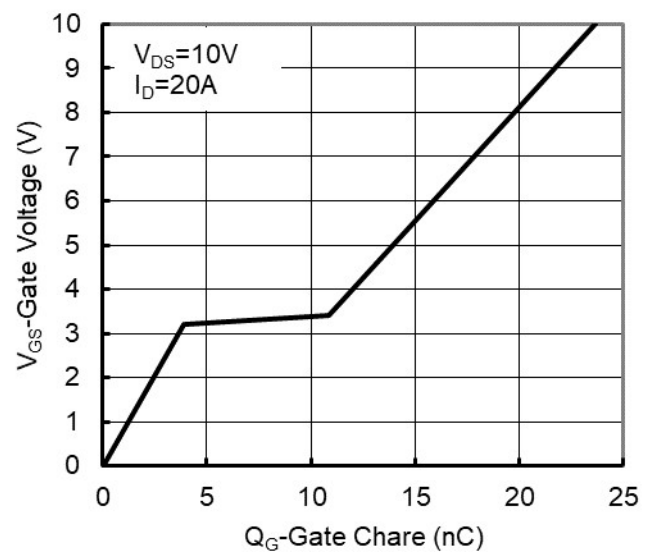


Figure6. Gate Charge

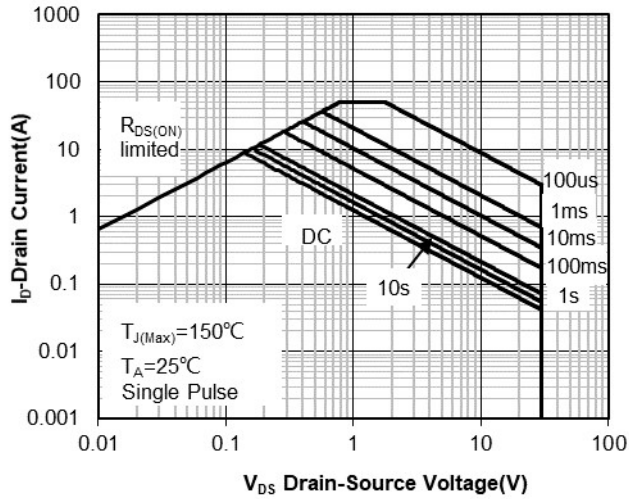


Figure7. Safe Operation Area

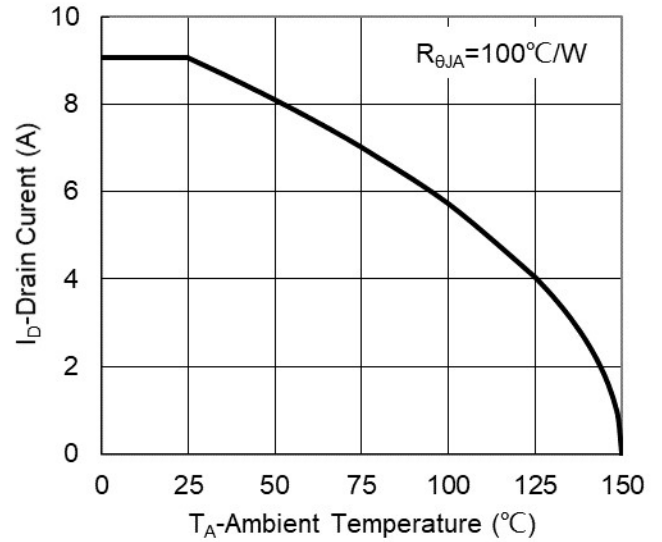


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

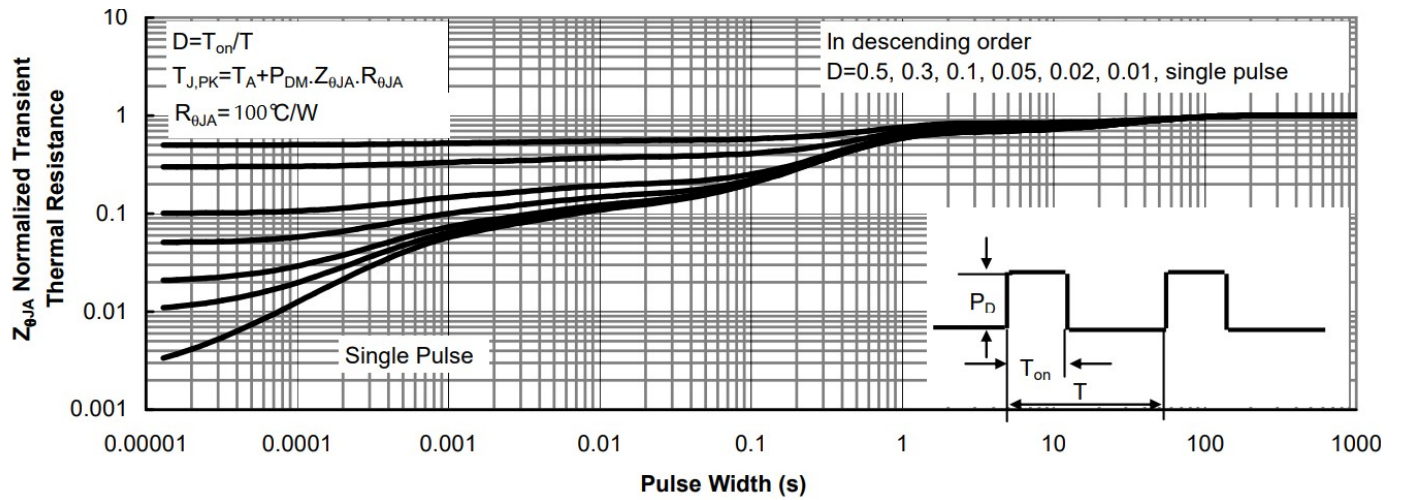
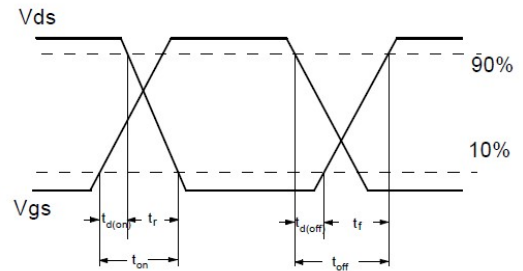
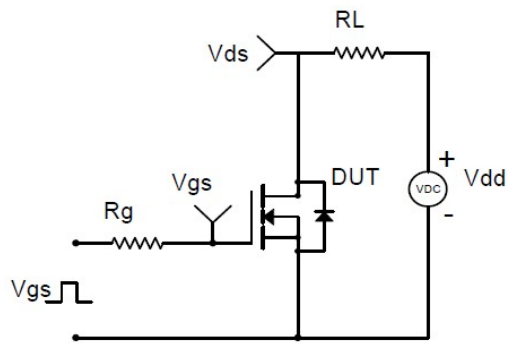
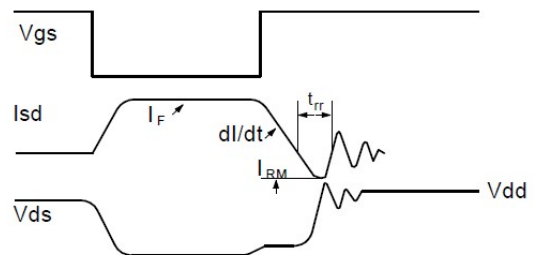
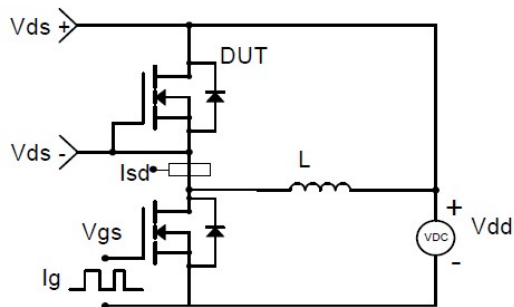


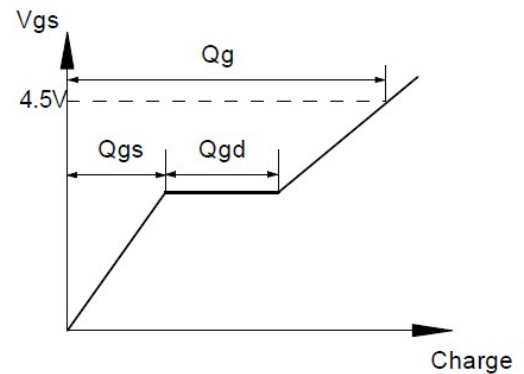
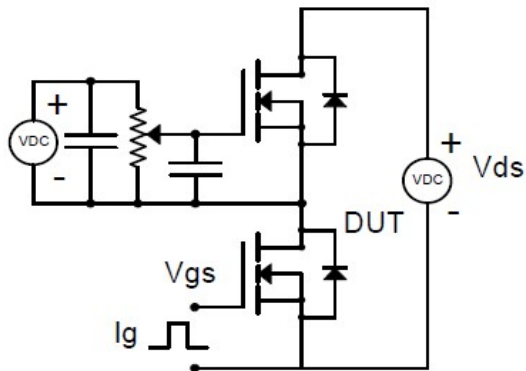
Figure9.Normalized Maximum Transient Thermal Impedance



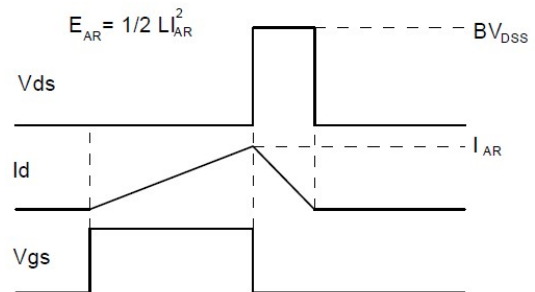
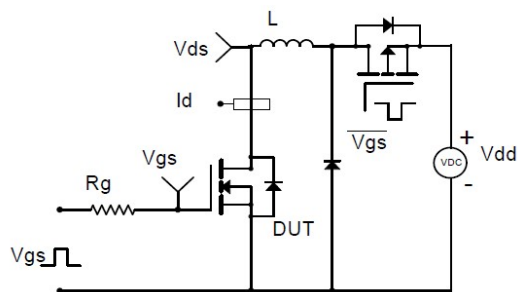
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

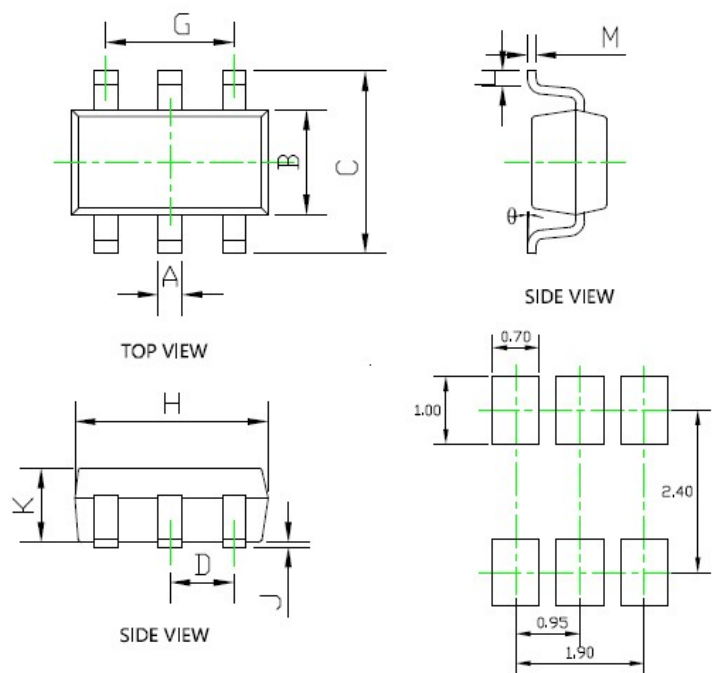


Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

■ SOT-23-6L Package information



Suggested Solder Pad Layout

Note:
 1. Controlling dimension in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
θ	0°	8°	0°	8°

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